



ALPHA & OMEGA
SEMICONDUCTOR



AOP607

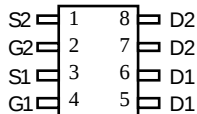
Complementary Enhancement Mode Field Effect Transistor

General Description

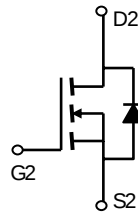
The AOP607 uses advanced trench technology MOSFETs to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs may be used in H-bridge, Inverters and other applications. *Standard Product AOP607 is Pb-free (meets ROHS & Sony 259 specifications). AOP607L is a Green Product ordering option. AOP607 and AOP607L are electrically identical.*

Features

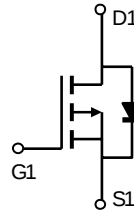
n-channel	p-channel
$V_{DS} (V) = 60V$	-60V
$I_D = 4.7A (V_{GS}=10V)$	-3.4A ($V_{GS}=-10V$)
$R_{DS(ON)}$	$R_{DS(ON)}$
$< 56m\Omega (V_{GS}=10V)$	$< 105m\Omega (V_{GS}=-10V)$
$< 77m\Omega (V_{GS}=4.5V)$	$< 135m\Omega (V_{GS}=-4.5V)$



PDIP-8



n-channel



p-channel

Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	V_{DS}	60	-60	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Continuous Drain Current ^A	$T_A=25^\circ C$	4.7	-3.4	A
	$T_A=70^\circ C$	3.8	-2.7	
Pulsed Drain Current ^B	I_{DM}	20	-20	
Power Dissipation	$T_A=25^\circ C$	2.5	2.5	W
	$T_A=70^\circ C$	1.6	1.6	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ C$

Thermal Characteristics: n-channel and p-channel

Parameter	Symbol	Device	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	n-ch	37	50	$^\circ C/W$
Maximum Junction-to-Ambient ^A		n-ch	74	90	$^\circ C/W$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	n-ch	28	40	$^\circ C/W$
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	p-ch	35	50	$^\circ C/W$
Maximum Junction-to-Ambient ^A		p-ch	73	90	$^\circ C/W$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	p-ch	32	40	$^\circ C/W$

N Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =48V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.5	2.3	3	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	20			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =4.7A T _J =125°C		42 75	56	mΩ
		V _{GS} =4.5V, I _D =4A		54	77	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =4.7A		11		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.78	1	V
I _S	Maximum Body-Diode Continuous Current				4	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, f=1MHz		450	540	pF
C _{oss}	Output Capacitance			60		pF
C _{rss}	Reverse Transfer Capacitance			25		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		1.65	2	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =30V, I _D =4.7A		8.5	10.5	nC
Q _g (4.5V)	Total Gate Charge			4.3	5.5	nC
Q _{gs}	Gate Source Charge			1.6		nC
Q _{gd}	Gate Drain Charge			2.2		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =30V, R _L =6Ω, R _{GEN} =3Ω		5.1		ns
t _r	Turn-On Rise Time			2.6		ns
t _{D(off)}	Turn-Off DelayTime			15.9		ns
t _f	Turn-Off Fall Time			2		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =4.7A, dI/dt=100A/μs		25.1	35	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =4.7A, dI/dt=100A/μs		28.7		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

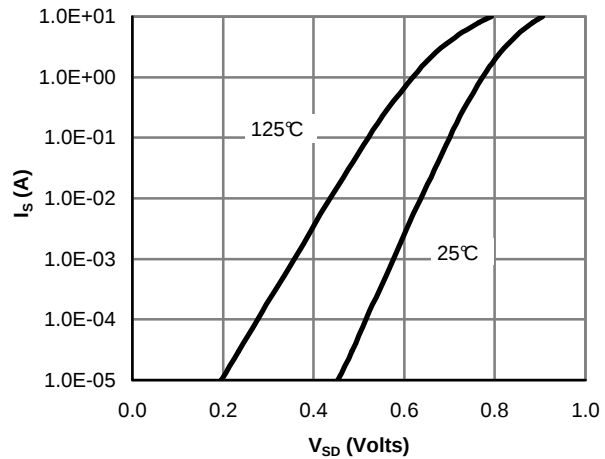
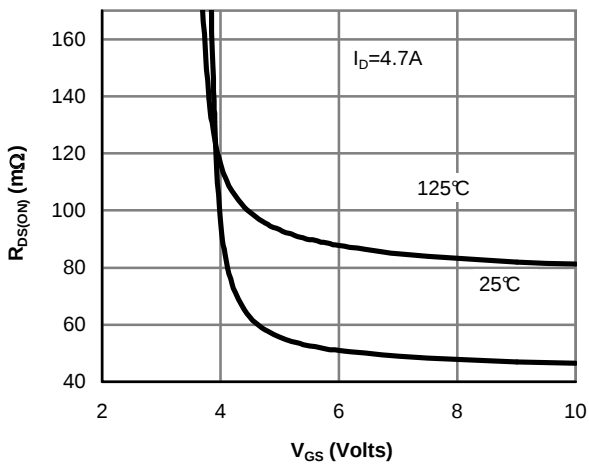
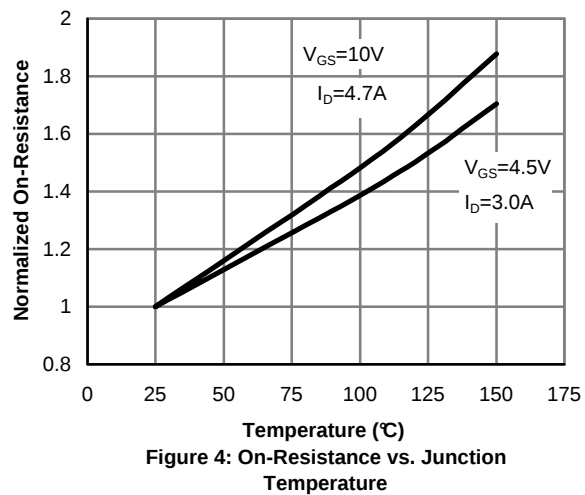
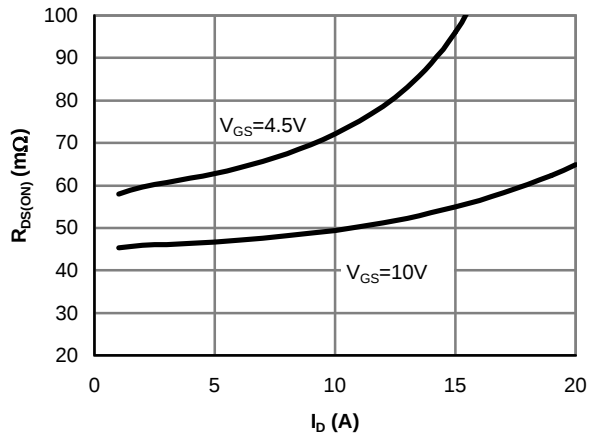
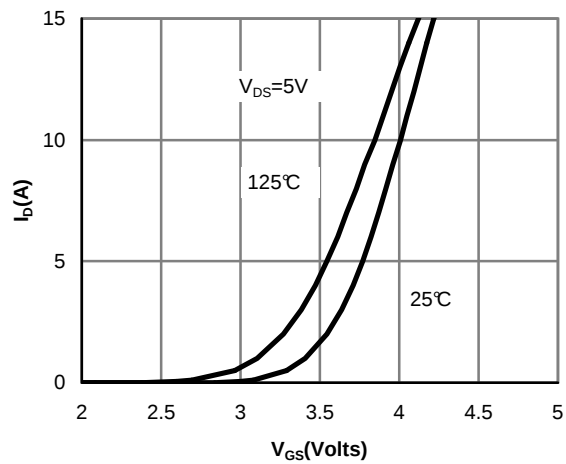
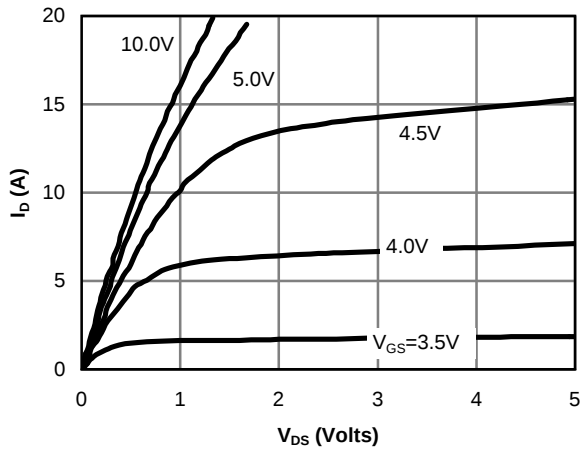
D: The static characteristics in Figures 1 to 6 are obtained using 80μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev 1 : Aug 2005

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: N-CHANNEL



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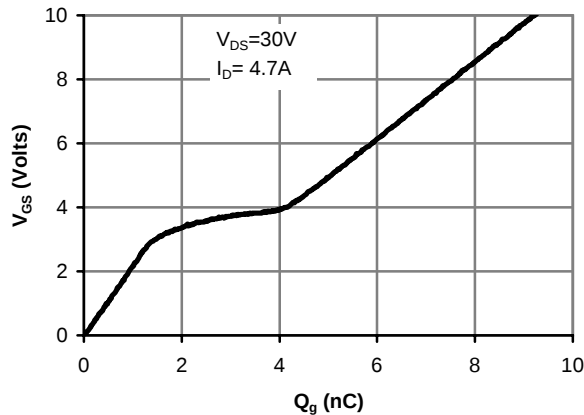


Figure 7: Gate-Charge Characteristics

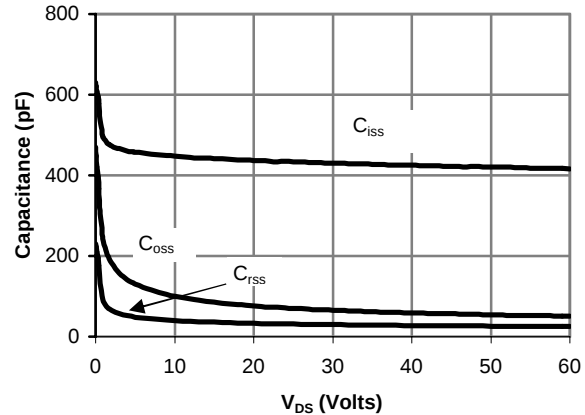


Figure 8: Capacitance Characteristics

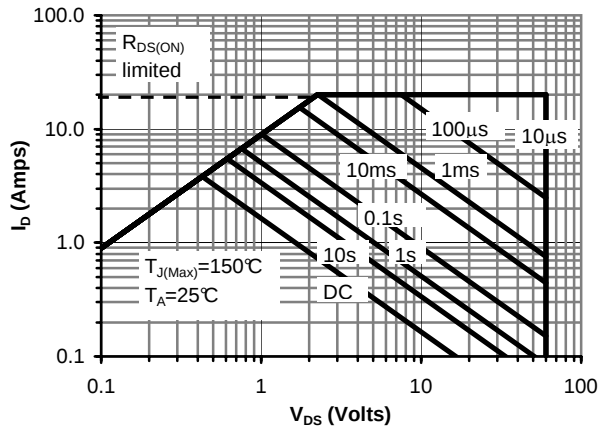


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

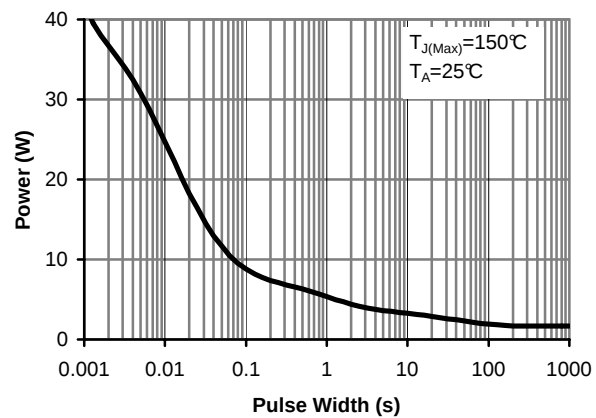


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

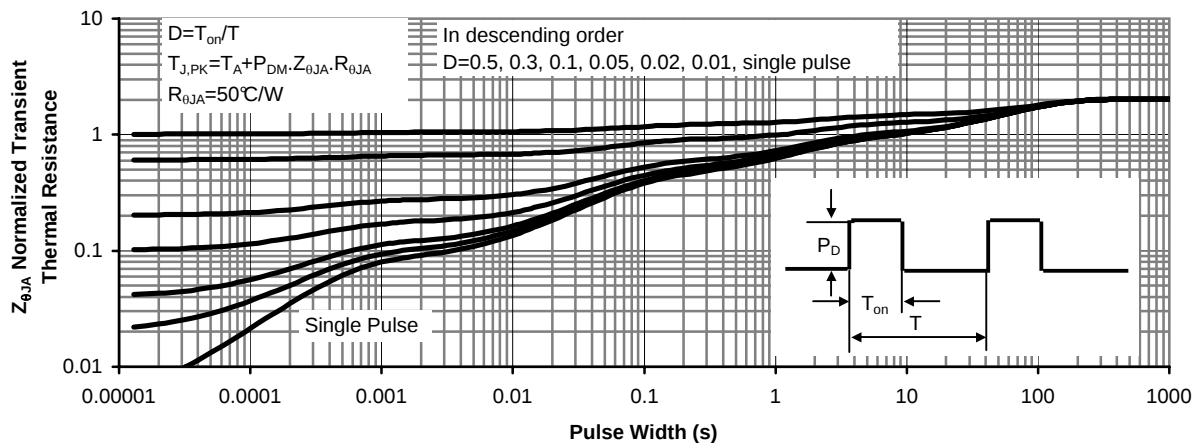


Figure 11: Normalized Maximum Transient Thermal Impedance

P-Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-48V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =-250μA	-1.5	-2.1	-3	V
I _{D(ON)}	On state drain current	V _{GS} =-10V, V _{DS} =-5V	-20			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-3.4A T _J =125°C		80 130	105	mΩ
		V _{GS} =-4.5V, I _D =-2.7A		102	135	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-3.4A		10		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.77	-1	V
I _S	Maximum Body-Diode Continuous Current				-4	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-30V, f=1MHz		930	1120	pF
C _{oss}	Output Capacitance			85		pF
C _{rss}	Reverse Transfer Capacitance			35		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		7.2	9	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge (10V)	V _{GS} =-10V, V _{DS} =-30V, I _D =-3.4A		16	20	nC
Q _g (4.5V)	Total Gate Charge (4.5V)			8	10	nC
Q _{gs}	Gate Source Charge			2.5		nC
Q _{gd}	Gate Drain Charge			3.2		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-10V, V _{DS} =-30V, R _L =8.8Ω, R _{GEN} =3Ω		8		ns
t _r	Turn-On Rise Time			3.8		ns
t _{D(off)}	Turn-Off DelayTime			31.5		ns
t _f	Turn-Off Fall Time			7.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-3.4A, dI/dt=100A/μs		27	35	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-3.4A, dI/dt=100A/μs		32		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

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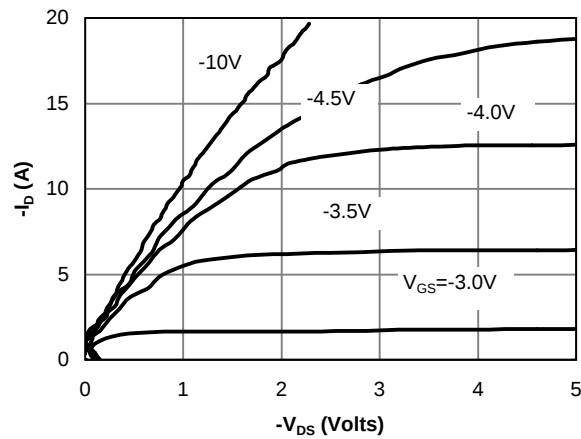


Fig 1: On-Region Characteristics

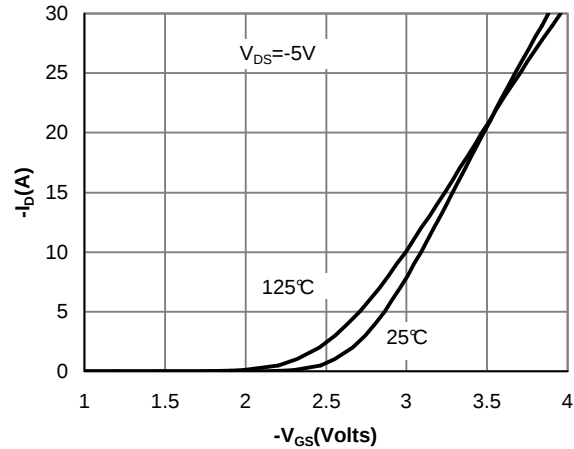


Figure 2: Transfer Characteristics

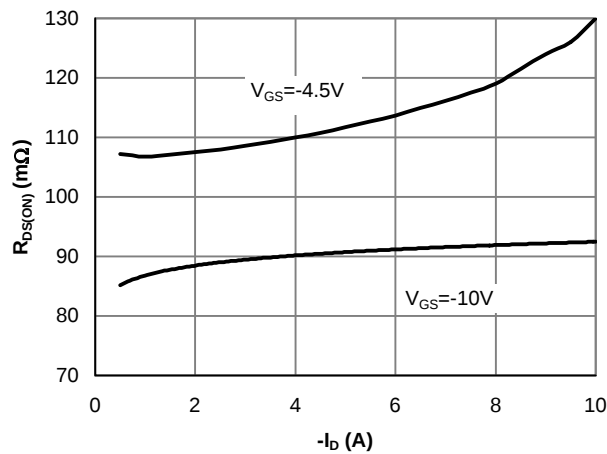


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

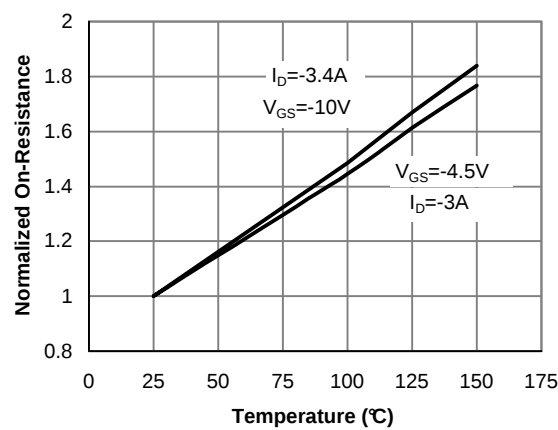


Figure 4: On-Resistance vs. Junction Temperature

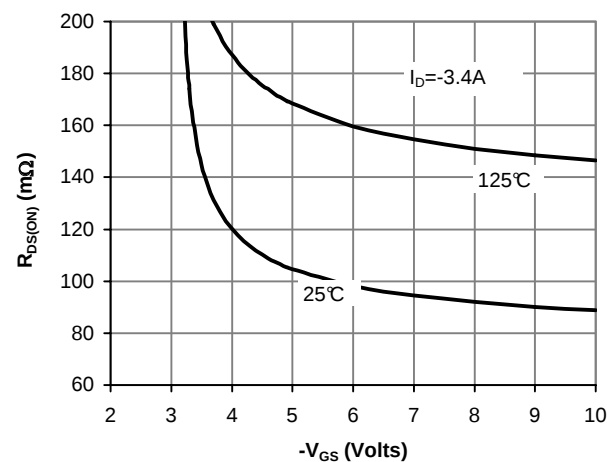


Figure 5: On-Resistance vs. Gate-Source Voltage

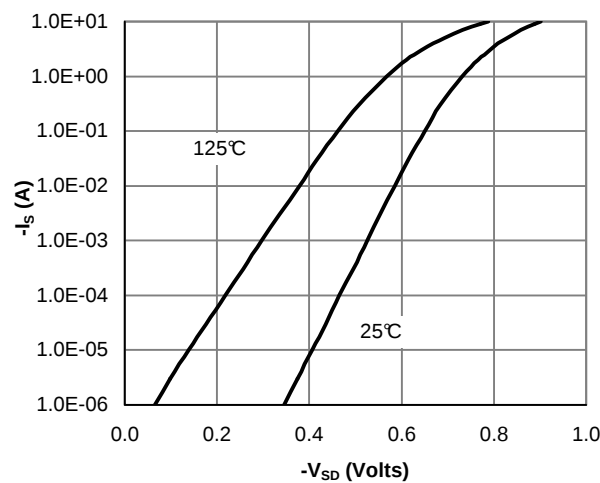


Figure 6: Body-Diode Characteristics

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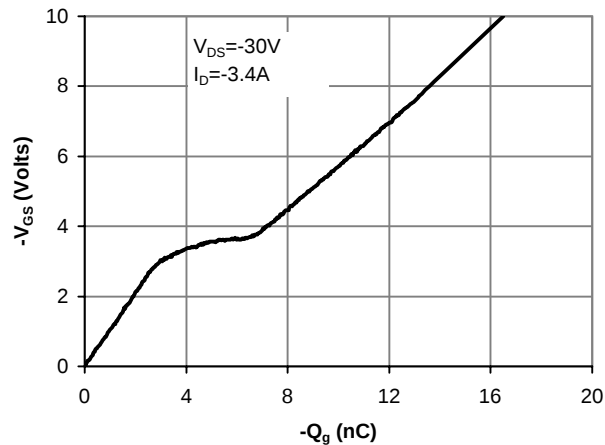


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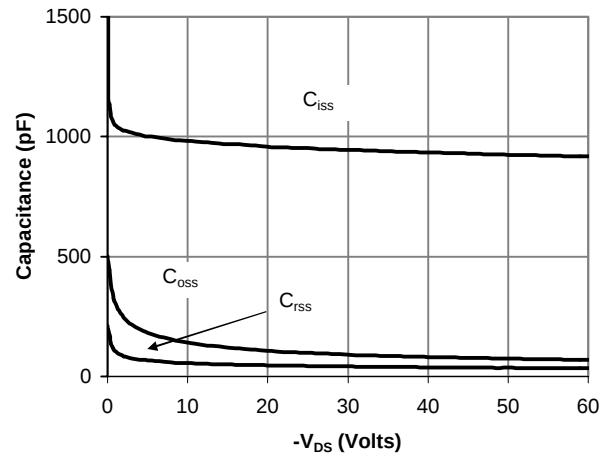


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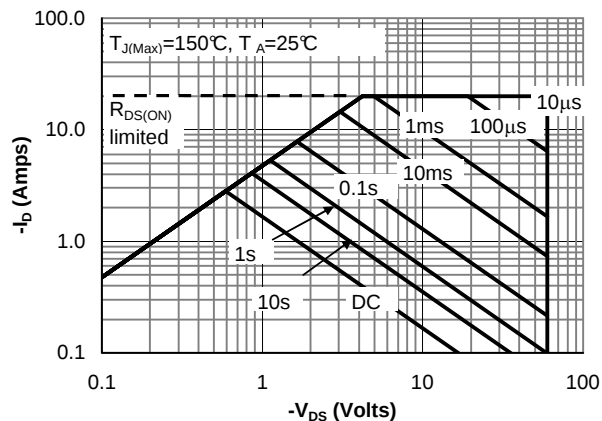


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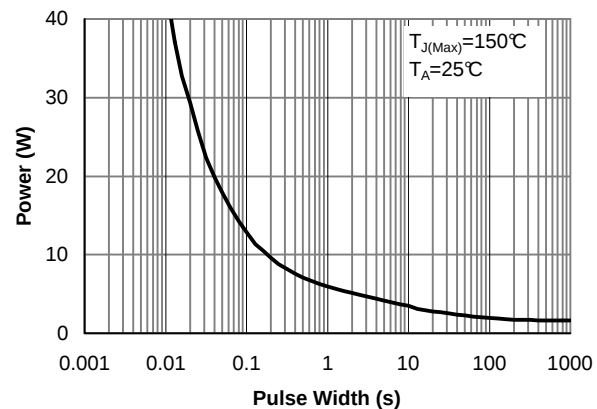


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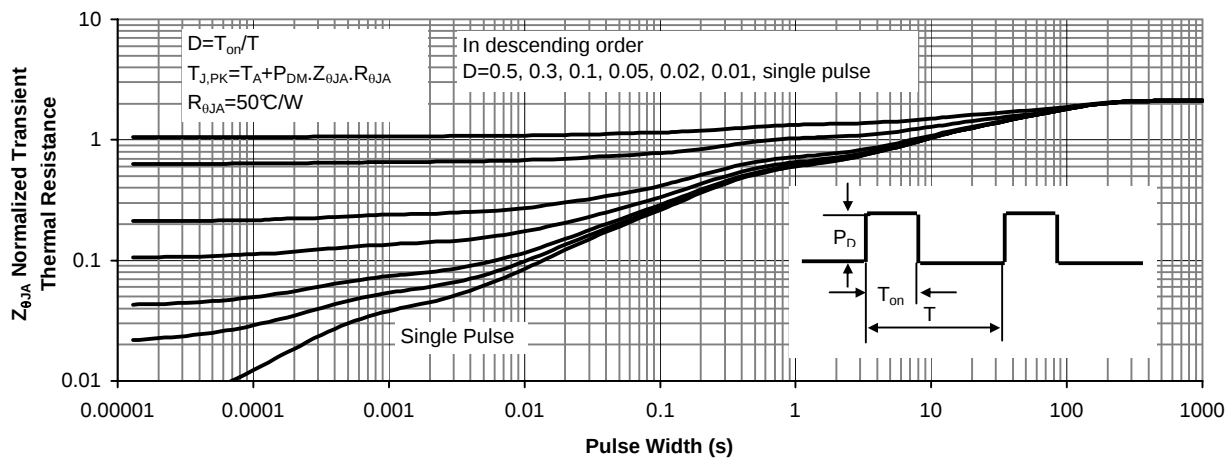


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